

TM03N10MI

N-Channel Enhancement Mosfet

General Description

- Low $R_{DS(ON)}$
- RoHS and Halogen-Free Compliant

Applications

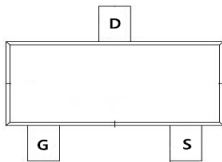
- Load switch
- PWM

General Features

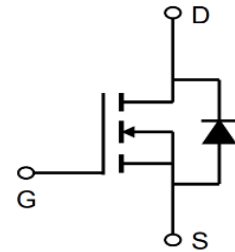
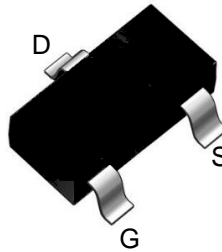
$V_{DS} = 100V$ $I_D = 3.0A$

$R_{DS(ON)} = 200m\Omega$ (typ.)@ $V_{GS}=10V$

100% UIS Tested
 100% R_g Tested



MI:SOT-23-3L



Marking: 3N10 OR 1002

Absolute Maximum Ratings (TC=25°C unless otherwise specified)

| Symbol | Parameter | Rating | Units |
|------------------------|--|------------|-------|
| V_{DS} | Drain-Source Voltage | 100 | V |
| V_{GS} | Gate-Source Voltage | ± 20 | V |
| $I_D @ T_A=25^\circ C$ | Continuous Drain Current, $V_{GS} @ 10V^1$ | 3 | A |
| $I_D @ T_A=70^\circ C$ | Continuous Drain Current, $V_{GS} @ 10V^1$ | 1.2 | A |
| I_{DM} | Pulsed Drain Current ² | 5 | A |
| $P_D @ T_A=25^\circ C$ | Total Power Dissipation ³ | 1 | W |
| T_{STG} | Storage Temperature Range | -55 to 150 | °C |
| T_J | Operating Junction Temperature Range | -55 to 150 | °C |

Thermal Data

| Symbol | Parameter | Typ. | Max. | Unit |
|-----------------|--|------|------|------|
| $R_{\theta JA}$ | Thermal Resistance Junction-ambient ¹ | --- | 125 | °C/W |
| $R_{\theta JC}$ | Thermal Resistance Junction-Case ¹ | --- | 80 | °C/W |

Electrical Characteristics (T_J=25°C unless otherwise specified)

| Parameter | Symbol | Test Condition | Min. | Typ. | Max. | Unit |
|---|----------------------|---|------|------|------|------|
| Static Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | V _{(BR)DSS} | V _{GS} = 0 V, I _D = 250μA | 100 | - | - | V |
| Gate Leakage Current | I _{GSS} | V _{GS} = ±20V, V _{DS} = 0V | - | - | ±100 | nA |
| Drain Cut-off Current | I _{DSS} | V _{DS} = 100V, V _{GS} = 0V | - | - | 1 | μA |
| Gate Threshold Voltage | V _{GS(th)} | V _{GS} = V _{DS} , I _D = 250μA | 1.1 | 1.5 | 2.5 | V |
| Drain-Source on-state Resistance ³ | R _{DS(on)} | V _{GS} = 10V, I _D = 2A | - | 200 | 230 | mΩ |
| | | V _{GS} = 4.5V, I _D = 1.5A | - | 220 | 280 | |
| Dynamic Characteristics⁴ | | | | | | |
| Input Capacitance | C _{iss} | V _{GS} = 0V, V _{DS} = 50V, f = 1MHz | - | 440 | - | pF |
| Output Capacitance | C _{oss} | | - | 14 | - | |
| Reverse Transfer Capacitance | C _{rss} | | - | 10 | - | |
| Switching Characteristics⁴ | | | | | | |
| Total gate charge | Q _g | V _{GS} = 10V, V _{DS} = 50V, I _D = 2A | - | 5.3 | - | nC |
| Gate-source charge | Q _{gs} | | - | 1.4 | - | |
| Gate-drain charge | Q _{gd} | | - | 1.8 | - | |
| Turn-on Time | t _{d(on)} | V _{GS} = 10V, V _{DD} = 50V, R _G = 1Ω, I _D = 2A | - | 14 | - | ns |
| Rise time | t _r | | - | 54 | - | |
| Turn-off Time | t _{d(off)} | | - | 18 | - | |
| Fall time | t _f | | - | 11 | - | |
| Source-Drain Diode characteristics | | | | | | |
| Body Diode Voltage ³ | V _{SD} | I _S = 1A, V _{GS} = 0V | - | - | 1.2 | V |
| Continuous Source Current | I _S | | - | - | 3.0 | A |

Notes:

1. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C.
2. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
3. Pulse Test: Pulse width≤300μs, duty cycle≤2%.
4. This value is guaranteed by design hence it is not included in the production test.

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Typical Characteristics

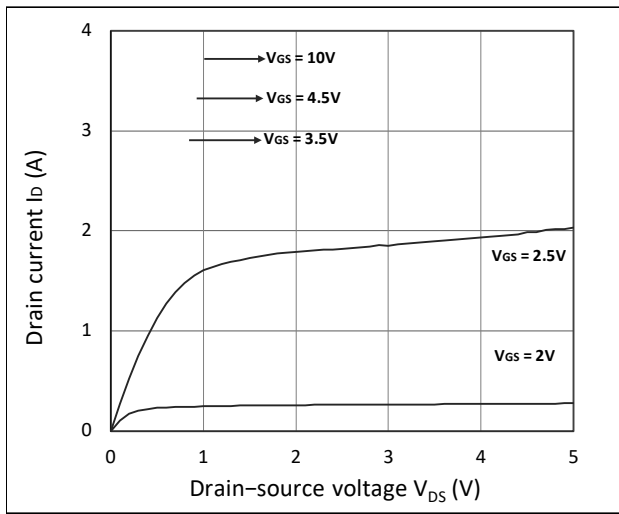


Figure 1. Output Characteristics

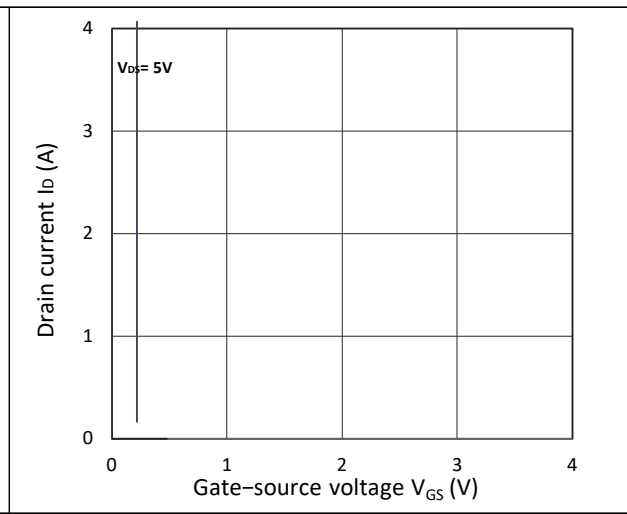


Figure 2. Transfer Characteristics

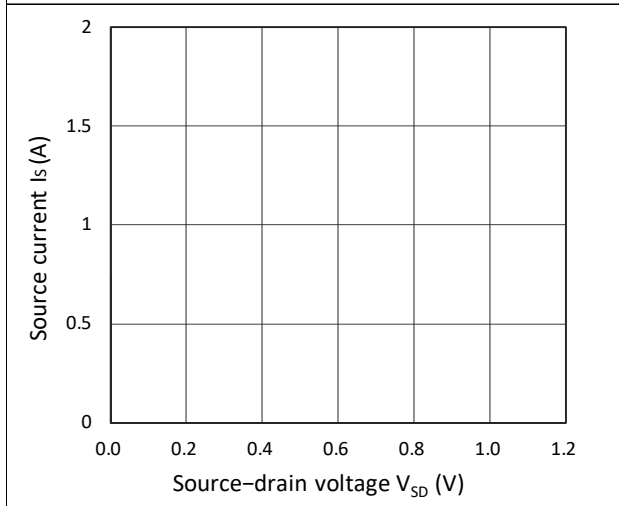


Figure 3. Forward Characteristics of Reverse

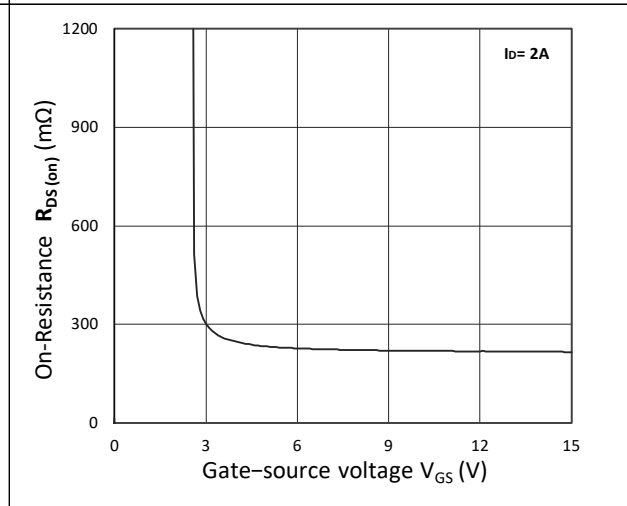


Figure 4. $R_{DS(on)}$ vs. V_{GS}

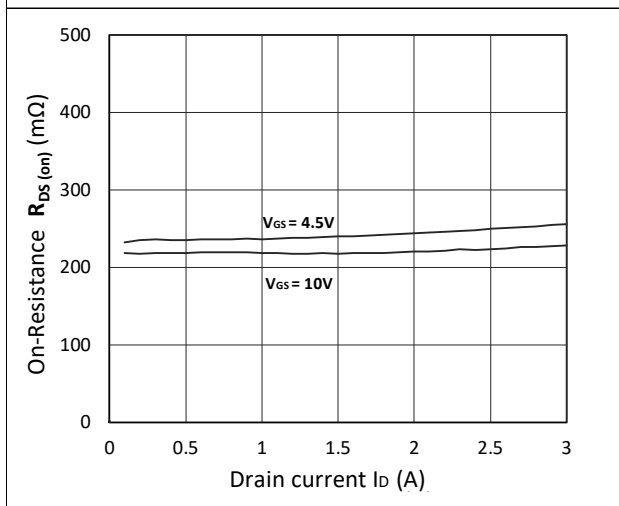


Figure 5. $R_{DS(on)}$ vs. I_D

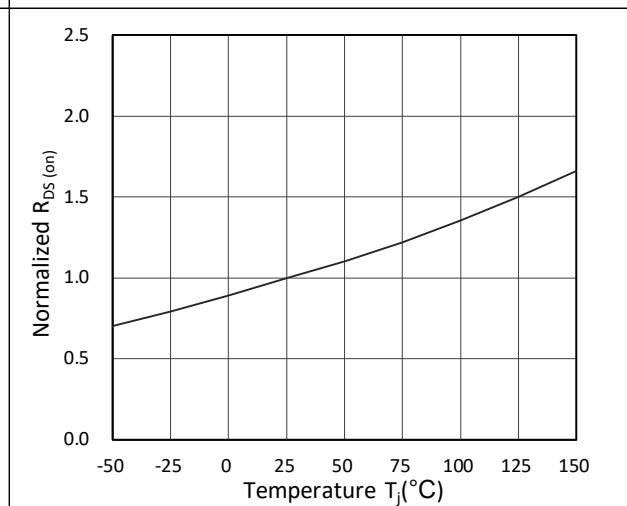


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

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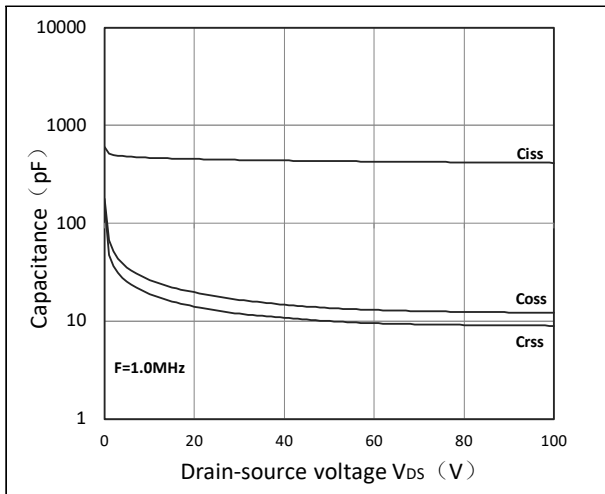


Figure 7. Capacitance Characteristics

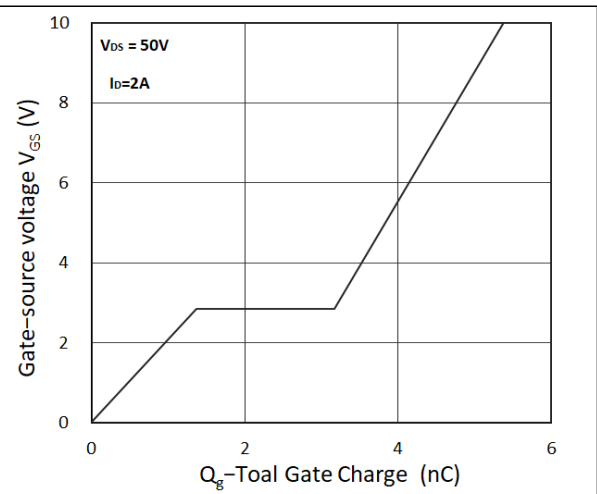
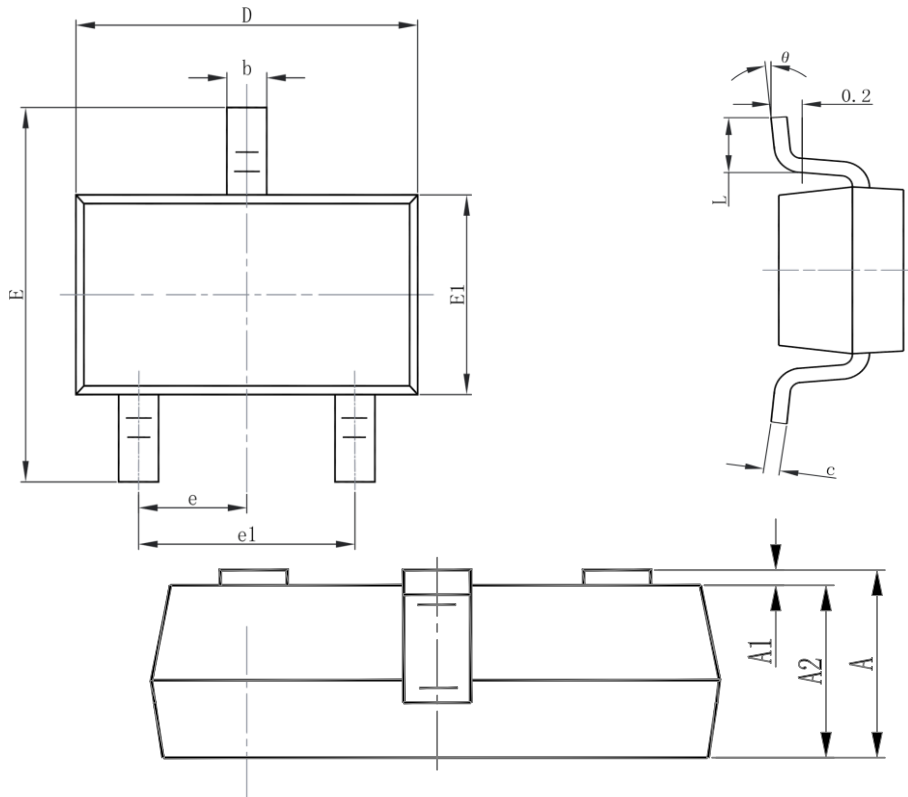


Figure 8. Gate Charge Characteristics

Package Information:SOT-23-3L



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|----------|---------------------------|-------|----------------------|-------|
| | Min. | Max. | Min. | Max. |
| A | 1.050 | 1.250 | 0.041 | 0.049 |
| A1 | 0.000 | 0.100 | 0.000 | 0.004 |
| A2 | 1.050 | 1.150 | 0.041 | 0.045 |
| b | 0.300 | 0.500 | 0.012 | 0.020 |
| c | 0.100 | 0.200 | 0.004 | 0.008 |
| D | 2.820 | 3.020 | 0.111 | 0.119 |
| E1 | 1.500 | 1.700 | 0.059 | 0.067 |
| E | 2.650 | 2.950 | 0.104 | 0.116 |
| e | 0.950(BSC) | | 0.037(BSC) | |
| e1 | 1.800 | 2.000 | 0.071 | 0.079 |
| L | 0.300 | 0.600 | 0.012 | 0.024 |
| θ | 0° | 8° | 0° | 8° |

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